

/ Descriptions

TO-251 N MOS N-CHANNEL MOSFET in a TO-251 Plastic Package.

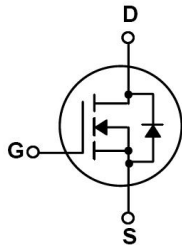
/ Features

Low thermal resistance, fast switching.

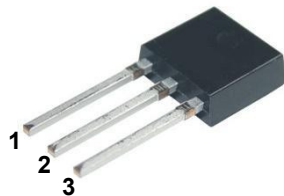
/ Applications

For Electronic transformer, Switch mode power supply.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S

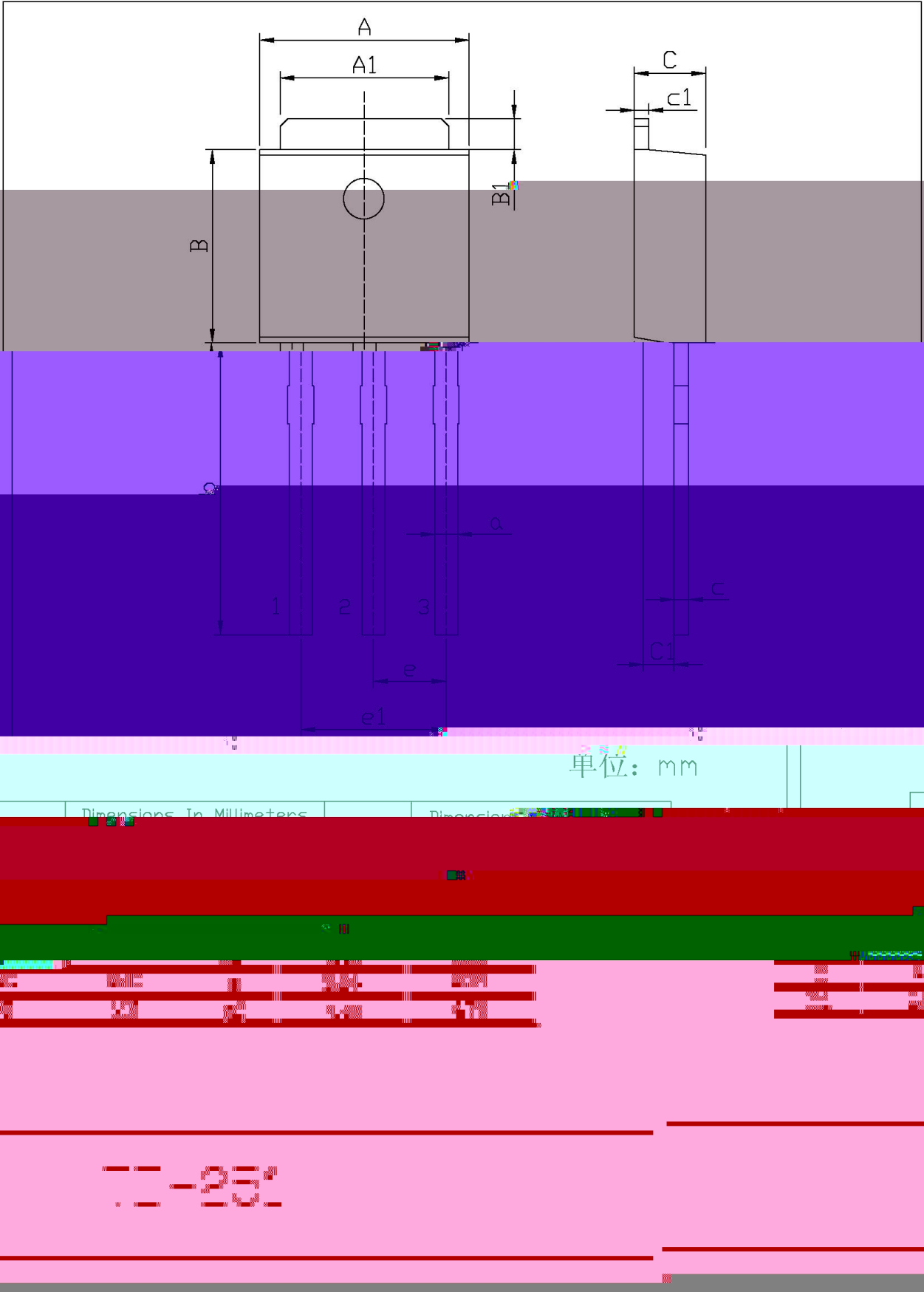
/ h_{FE} Classifications & Marking

See Marking Instructions.

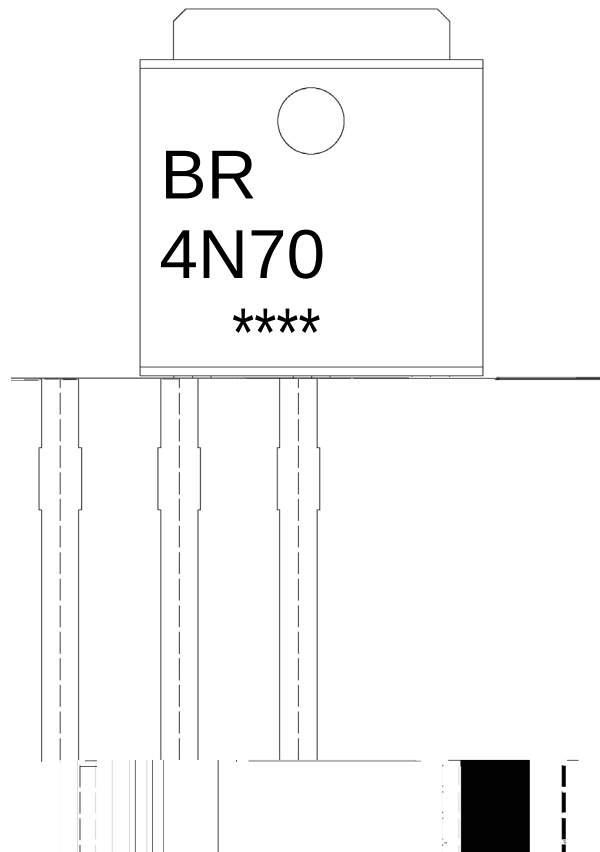
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	700	V
Gate-Source Voltage	V_{GS}	± 30	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	4.0	A
Drain Current	$I_D(T_c=100^\circ\text{C})$	2.5	A
Drain Current - Pulsed	I_{DM}	16	A
Single Pulsed Avalanche Energy	E_{AS}	260	mJ
Power Dissipation	P_{tot}	106	W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	
Thermal Resistance Junction-case	$R_{\theta-JC}$	1.18	/W
Thermal Resistance Junction-ambient	$R_{\theta-JA}$	62.5	/W

Ω G

/ Package Dimensions



/ **Marking Instructions**



BR

4N70

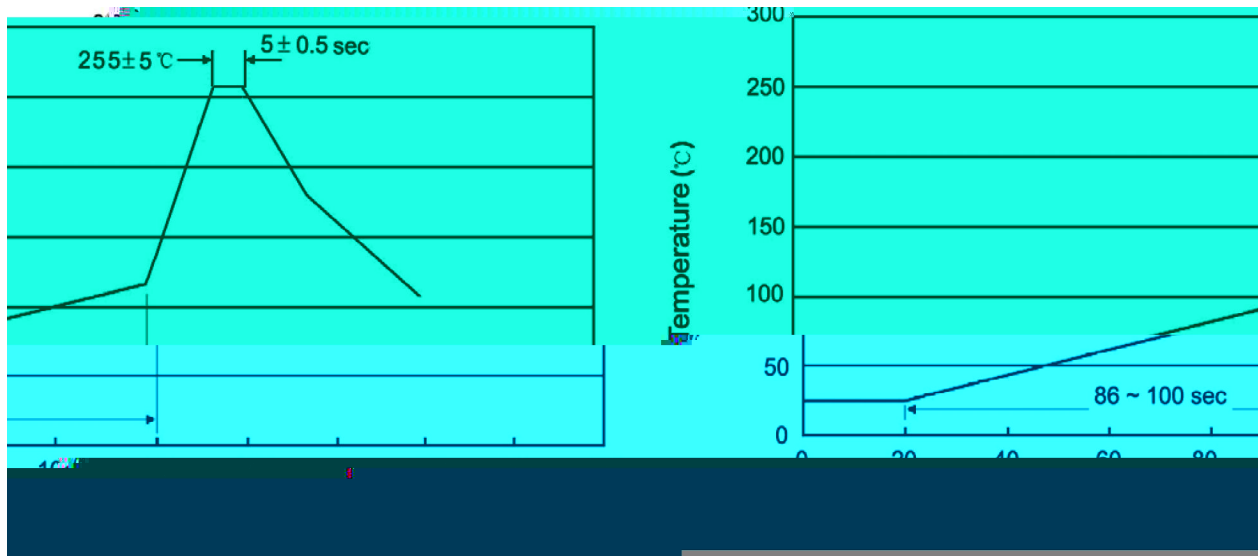
Note:

BR: Company Code

4N70: Product Type.

****: Lot No. Code, code change with Lot No.

() / **Temperature Profile for Dip Soldering(Pb-Free)**



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ **Resistance to Soldering Heat Test Conditions**

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ **Packaging SPEC.**

/ **BULK**

Package Type	Units					Dimension (unit mm ³)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-251	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195

/ **TUBE**

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

/ **Notices**